



安徽富信半导体科技有限公司

ANHUI FOSAN SEMICONDUCTOR TECHNOLOGY CO., LTD.

MURS320B-MURS360B

SMB Super Fast Recovery Diode 超快恢复二极管

■Features 特点

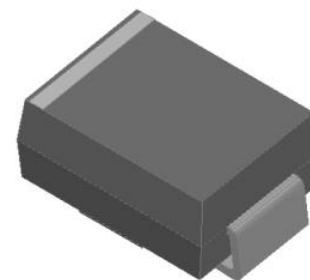
Glass passivated chip junction 玻璃钝化芯片保护结

High forward surge capability 高正向浪涌能力

Super Fast Recovery time 超快恢复时间

Surface Mount Device 表面贴装器件

Case 封装:SMB



■Maximum Rating 最大额定值

($T_A=25^{\circ}\text{C}$ unless otherwise noted 如无特殊说明, 温度为 25°C)

Characteristic 特性参数	Symbol 符号	MURS320B	MURS340B	MURS360B	Unit 单位
Repetitive Peak Reverse Voltage 重复峰值反向电压	V_{RRM}	200	400	600	V
DC Reverse Voltage 直流反向电压	V_R	200	400	600	V
RMS Reverse Voltage 反向电压均方根值	$V_{R(RMS)}$	140	280	420	V
Forward Rectified Output Current 正向整流电流	I_O	3			A
Peak Surge Current 峰值浪涌电流	I_{FSM}	100			A
Thermal Resistance J-A 结到环境热阻	$R_{\theta JA}$	60			$^{\circ}\text{C}/\text{W}$
Junction/Storage Temperature 结温/储藏温度	T_J, T_{stg}	-50to+150 $^{\circ}\text{C}$			$^{\circ}\text{C}$

■Electrical Characteristics 电特性

($T_A=25^{\circ}\text{C}$ unless otherwise noted 如无特殊说明, 温度为 25°C)

Characteristic 特性参数	Symbol 符号	MURS320B	MURS340B	MURS360B	Unit 单位	Condition 条件
Forward Voltage 正向电压	V_F	0.92	1.25		V	$I_F=3\text{A}$
Reverse Current 反向电流	I_R	5($T_A=25^{\circ}\text{C}$) 50($T_A=125^{\circ}\text{C}$)			μA	$V_R=V_{RRM}$
Reverse Recovery Time 反向恢复时间	T_{rr}	35	50		nS	$I_F=0.5\text{A}, I_R=1\text{A}$ $I_{rr}=0.25\text{A}$
Avalanche energy 雪崩能量	E_{AS}	6.6	4.8		mJ	$I_R=0.8\text{A}, L=15\text{mH}$
Junction Capacitance 结电容	C_J	63	55	50	pF	$V_R=4\text{V}, f=1\text{MHz}$

■ Typical Characteristic Curve 典型特性曲线

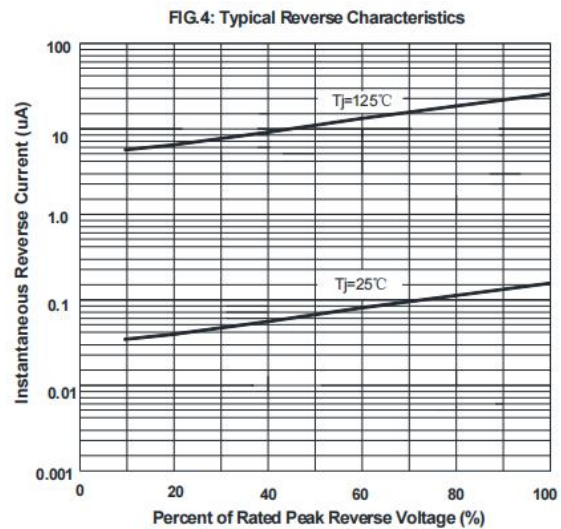
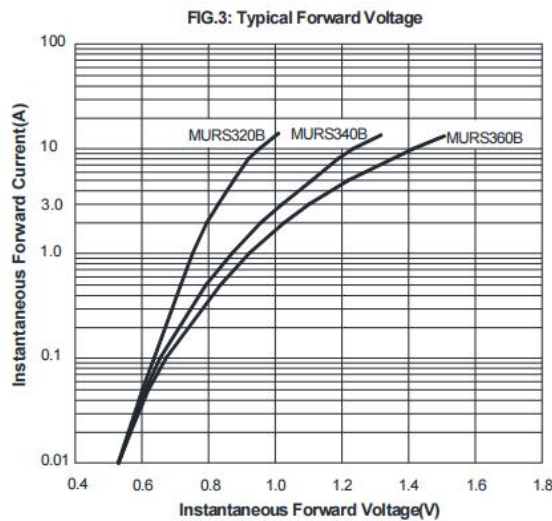
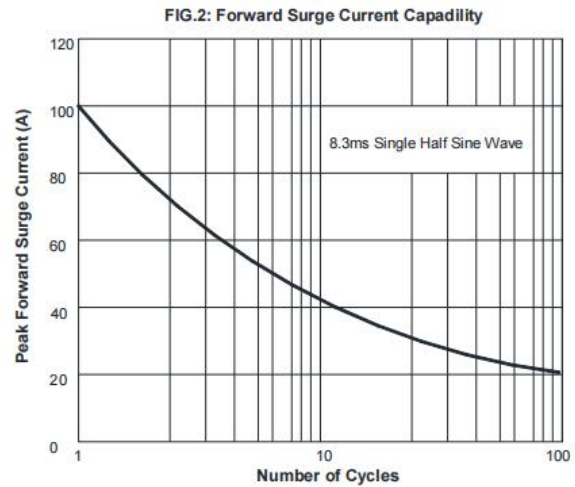
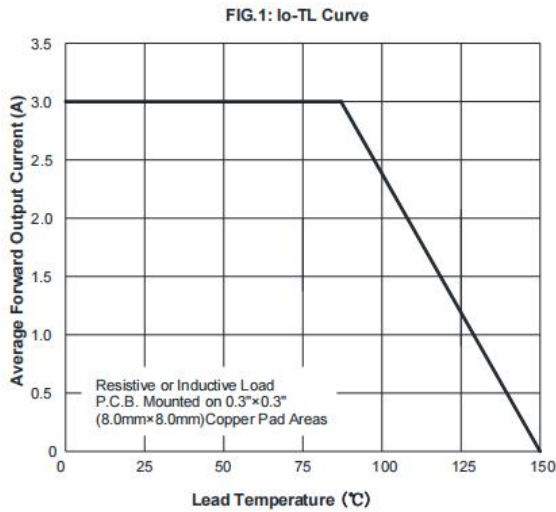
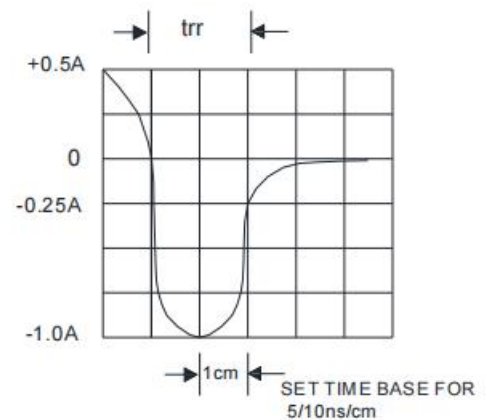
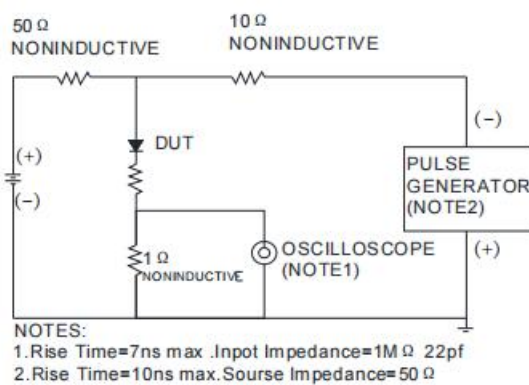
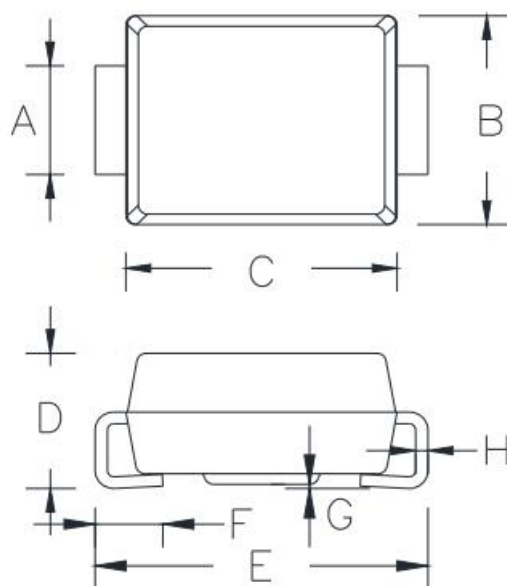


FIG.5: Diagram of circuit and Testing wave form of reverse recovery time



■Dimension 外形封装尺寸

DO-214AA(SMB)



Dimensions in millimeters

DO-214AA(SMB)		
Dim	Min	Max
A	1.85	2.15
B	3.30	3.94
C	4.05	4.75
D	1.99	2.61
E	5.21	5.59
F	0.90	1.41
G	0.10	0.20
H	0.15	0.31